FAIRCHILD SEMICONDUCTOR®

January 2008

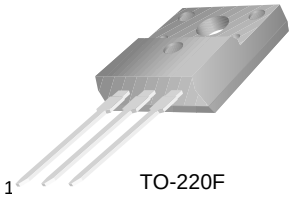
FJPF5200
NPN Epitaxial Silicon Transistor

Applications

- High-Fidelity Audio Output Amplifier
- General Purpose Power Amplifier

Features

- High Current Capability: I_C = 15A.
- High Power Dissipation : 50watts.
- High Fequency : 30MHz.
- High Voltage : V_{CEO}=230V
- Wide S.O.A for reliable operation.
- Excellent Gain Linearity for low THD.
- Complement to FJPF1943
- Thermal and electrical Spice models are available.
- Same transistor is also available in:
  -- TO264 package, 2SC5200/FJL4315 : 150 watts
  -- TO3P package, 2SC5242/FJA4313 : 130 watts
  -- TO220 package, FJP5200 : 80 watts



TO-220F

1.Base 2.Collector 3.Emitter

Absolute Maximum Ratings* T_a = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
BV_{CBO}	Collector-Base Voltage	230	V
BV_{CEO}	Collector-Emitter Voltage	230	V
BV_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current(DC)	15	A
I_B	Base Current	1.5	A
P_D	Total Device Dissipation(T_C=25°C) Derate above 25°C	50 0.4	W W/°C
T_J, T_{STG}	Junction and Storage Temperature	- 50 ~ +150	°C

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.5	°C/W

* Device mounted on minimum pad size

h_{FE} Classification

Classification	R	O
h_{FE1}	55 ~ 110	80 ~ 160

Electrical Characteristics* T_a=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C=5mA, I_E=0	230			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C=10mA, R_{BE}=∞	230			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E=5mA, I_C=0	5			V
I_{CBO}	Collector Cut-off Current	V_{CB}=230V, I_E=0			5.0	μA
I_{EBO}	Emitter Cut-off Current	V_{EB}=5V, I_C=0			5.0	μA
h_{FE1}	DC Current Gain	V_{CE}=5V, I_C=1A	55		160	
h_{FE2}	DC Current Gain	V_{CE}=5V, I_C=7A	35	60		
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C=8A, I_B=0.8A		0.4	3.0	V
V_{BE}(on)	Base-Emitter On Voltage	V_{CE}=5V, I_C=7A		1.0	1.5	V
f_T	Current Gain Bandwidth Product	V_{CE}=5V, I_C=1A		30		MHz
C_{ob}	Output Capacitance	V_{CB}=10V, f=1MHz		200		pF

* Pulse Test: Pulse Widt=20μs, Duty Cycle≤2%

Ordering Information

Part Number	Marking	Package	Packing Method	Remarks
FJPF5200RTU	J5200R	TO-220F	TUBE	hFE1 R grade
FJPF5200OTU	J5200O	TO-220F	TUBE	hFE1 O grade

Typical Characteristics

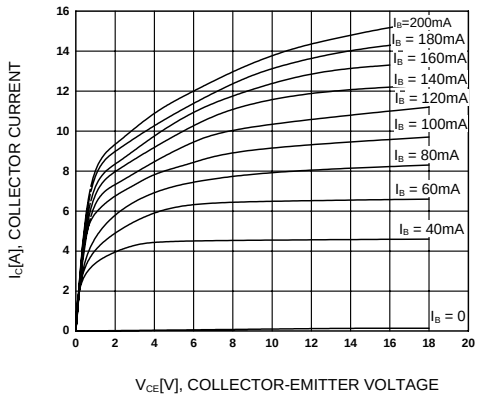


Figure 1. Static Characteristic

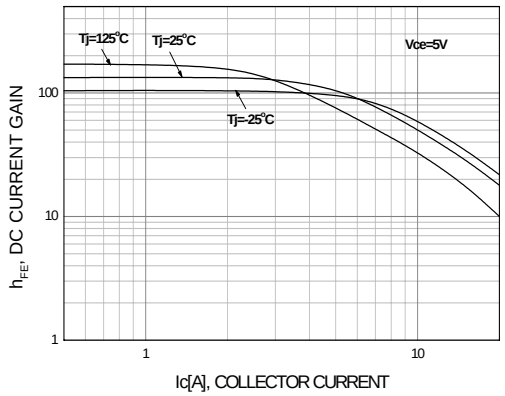


Figure 2. DC current Gain

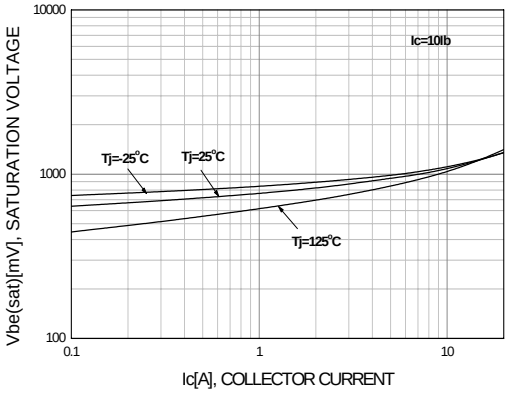


Figure 3. Base-Emitter Saturation Voltage

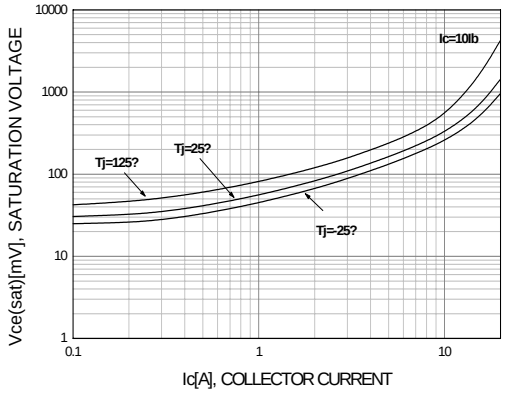


Figure 4. Collector-Emitter Saturation Voltage

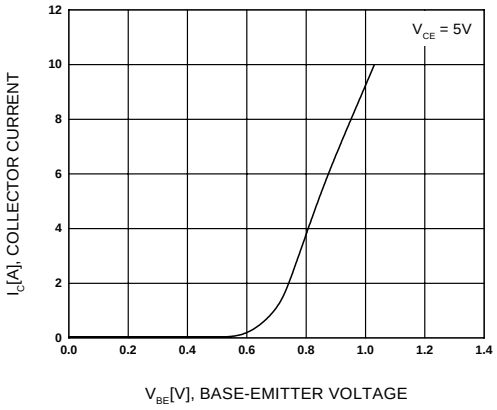


Figure 5. Base-Emitter On Voltage

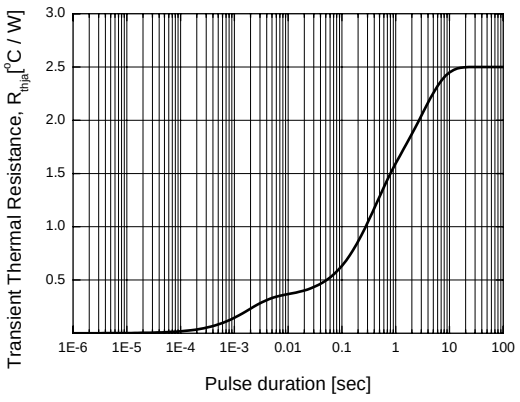


Figure 6. Thermal Resistance

Typical Characteristics

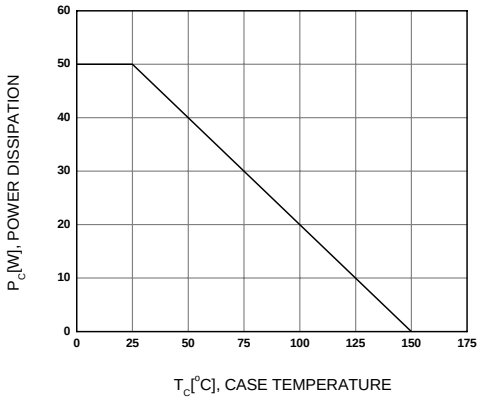


Figure 7. Power Derating

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